

Electronic Supplementary Information for

Mechanical exfoliation and electrical characterization of one-dimensional Nb₂Se₉ atomic crystal

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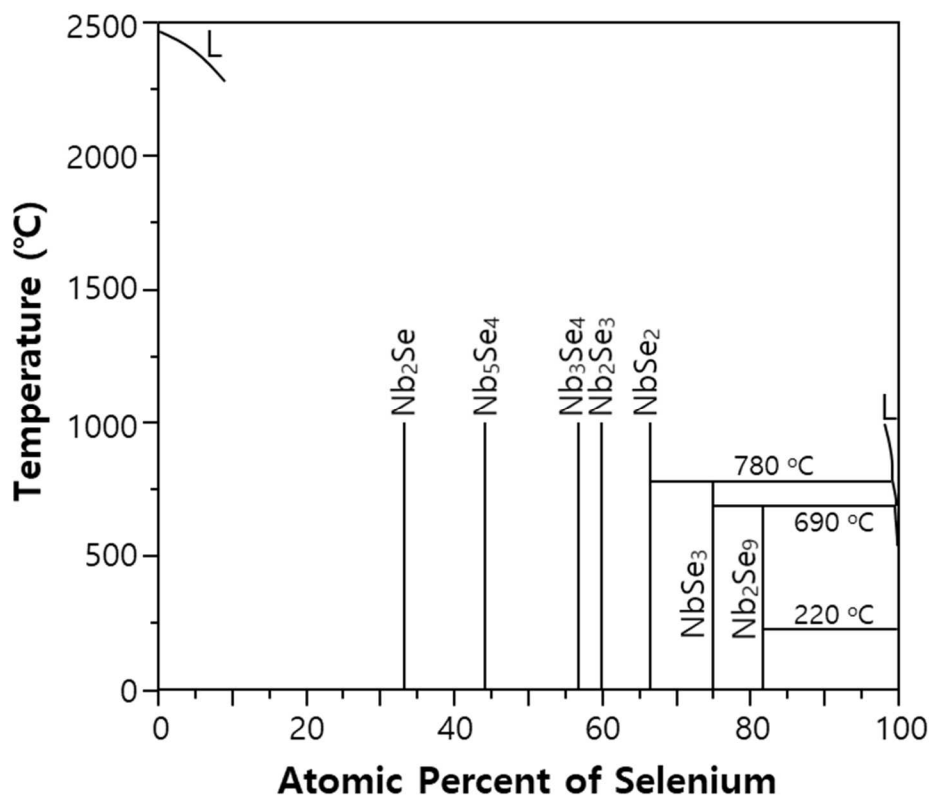


Figure S1. Phase diagram of Nb-Se binary system.

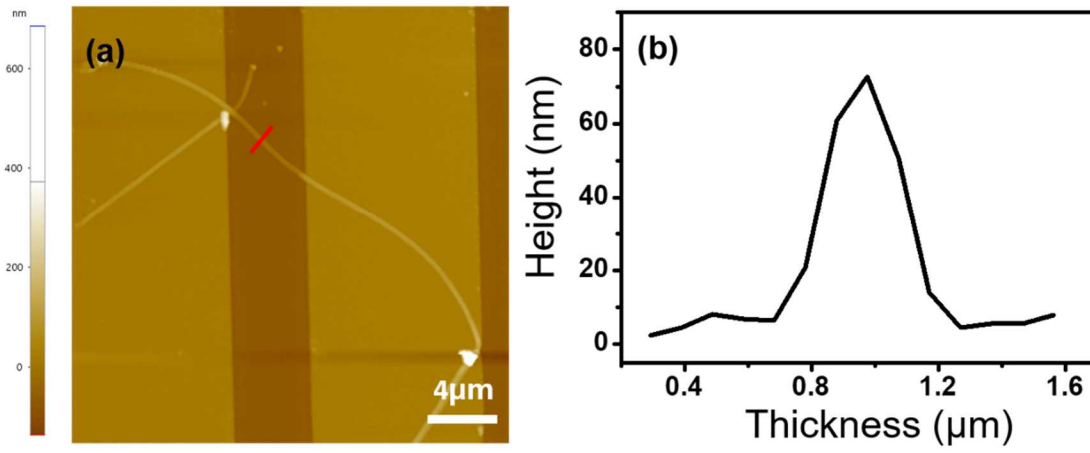


Figure S2. (a) AFM image of the Nb₂Se₉ FET. (b) Line profile of the corresponding Nb₂Se₉ flake, as marked in (a)